UNISONIC TECHNOLOGIES CO., LTD

UTP2012Z

PNP EPITAXIAL SILICON TRANSISTOR

55V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

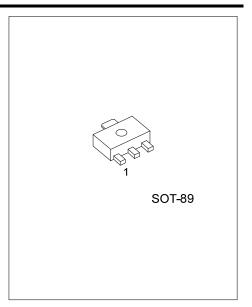
DESCRIPTION

The UTP2012Z is an PNP low $V_{\text{CE}(\text{SAT})}$ Breakthrough In Small Signal (BISS) transistor in a medium power.

NPN complement: UTN2010Z.

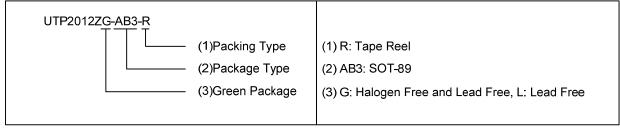
■ FEATURES

- * Very low collector-emitter saturation voltage V_{CE(SAT)}
- * High collector current capability IC and ICM
- * High collector current gain (hFE) at high IC
- * High energy efficiency due to less heat generation
- * Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

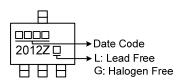


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTP2012ZL-AB3-R	UTP2012ZG-AB3-R	SOT-89	В	С	Е	Tape Reel	



MARKING



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■ ABSOLUATE MAXIUM RATINGS (T_A= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-55	V
Emitter to Base Voltage	V_{EBO}	-7	V
Bese Current	I _B	-2	Α
Collector Current	Ic	-4.3	Α
Peak Collector Current (t _P ≤1ms)	I _{CM}	-15	Α
Collector Dissipation	Pc	1.5	W
Junction Temperature	T_J	-40 ~ +150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Single pulse, P_W=10ms.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout. (25×25×1.6mm)

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θЈА	83	°C/W

Note: Device mounted on FR-4 PCB with minimum recommended pad layout. (25×25×1.6mm).

■ ELECTRICAL CHARACTERISTICS (T_A= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA	-100			V
Collector-Emitter Breakdown Voltage	BV _{CER}	I _C =-1μA, RB≤1kΩ	-100			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA	-55			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA	-7.0			V
Collector-Base Cut-off Current	Ісво	V _{CB} =-80V, I _E =0A			-20	nA
		V _{CB} =-80V, I _E =0A, T _A =100°C			-500	nA
Collector-Emitter Cut-off Current	Icer	V _{CE} =-80V, RB≤1kΩ			-20	nA
Emitter-Base Cut-off Current	I _{ЕВО}	V _{EB} =-6V, I _C =0A			-10	nA
Base-Emitter On Voltage (Note)	V _{BE} (ON)	V _{CE} =-1V, I _C =-5A			-950	mV
Base-Emitter Saturation Voltage	V _{BE} (SAT)	Ic=-5A, I _B =-500mA			-1050	mV
(Note)	V BE (SAT)	IC5A, IB500MA			-1030	
Collector-Emitter Saturation Voltage (Note)	VCE(SAT)	I _C =-100mA, I _B =-10mA			-20	mV
		I _C =-1A, I _B =-100mA			-65	mV
		I _C =-2A, I _B =-200mA			-110	mV
		Ic=-5A, Iв=-500mA			-300	mV
	hfE	Ic=-10mA, VcE=-1V	100			
DC Current Transfer Ratio (Note)		Ic=-2A, VcE=-1V	100		300	
		Ic=-5A, Vc==-1V	45			
		I _C =-10A, V _{CE} =-1V	10			
Transition Frequency (Note)	f⊤	I _C =-100mA, V _{CE} =-10V, f=50MHz		120		MHz
Collector Capacitance	Сов	V _{CB} =-10V, f=1MHz		90		pF
Turn-on Time	ton			280		ns
Turn-off Time	toff	I _C =-0.1A, V _{CC} =-1V, I _{B1} = I _{B2} =-10mA		15		μS
Storage Time	ts			14.9		μS
Fall Time	tf			97		ns

Note: Measured under pulsed conditions. Pulse Test: Pulse width \leq 300 μ s, Duty cycle \leq 2%.

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